

Electrolytic Etching Cell Fluid Dynamics

a

Finite Element Analysis (FEA)

using

flexPDE

Craig E. Nelson - Consultant Engineer

Partial Differential Equation Formulation for Fluid Dynamic Finite Element Analysis (FEA)

The Navier-Stokes equation for steady incompressible flow in two Cartesian dimensions is

$$\text{dens}*(dt(U) + U*dx(U) + V*dy(U)) = \text{visc}*del2(U) - dx(P) + \text{dens}*Fx$$

$$\text{dens}*(dt(V) + U*dx(V) + V*dy(V)) = \text{visc}*del2(V) - dy(P) + \text{dens}*Fy$$

together with the continuity equation

$$\text{div}[U,V] = 0$$

where U and V are the X- and Y- components of the flow velocity

P is the fluid pressure

dens is the fluid density

visc is the fluid viscosity

Fx and Fy are the X- and Y- components of the body force.

In order to derive a third equation for the Pressure variable, we differentiate the U-equation with respect to X and the V-equation with respect to Y. Using the continuity equation to eliminate terms, we get

$$\text{del2}(P) = 2*\text{dens}*[dx(U)*dy(V) - dy(U)*dx(V)]$$

Although this equation is consistent with the continuity equation, it does not enforce it. However, since $\text{div}[U,V] = 0$, we are free to add it at will to the pressure equation. A negative value of $\text{div}[U,V]$ implies the destruction of material, so we need a positive pressure to oppose the flow. This implies a modified pressure equation

$$\text{del2}(P) = 2*\text{dens}*[dx(U)*dy(V) - dy(U)*dx(V)] + L*(dx(U)+dy(V))$$

where L is a "large" number chosen to enforce "sufficient" compliance with the material conservation equation.

Setting U and V equal to zero in the U and V equations to reflect the conditions on a no-slip boundary, we get

$$dx(P) = \text{visc}*del2(U)$$

$$dy(P) = \text{visc}*del2(V)$$

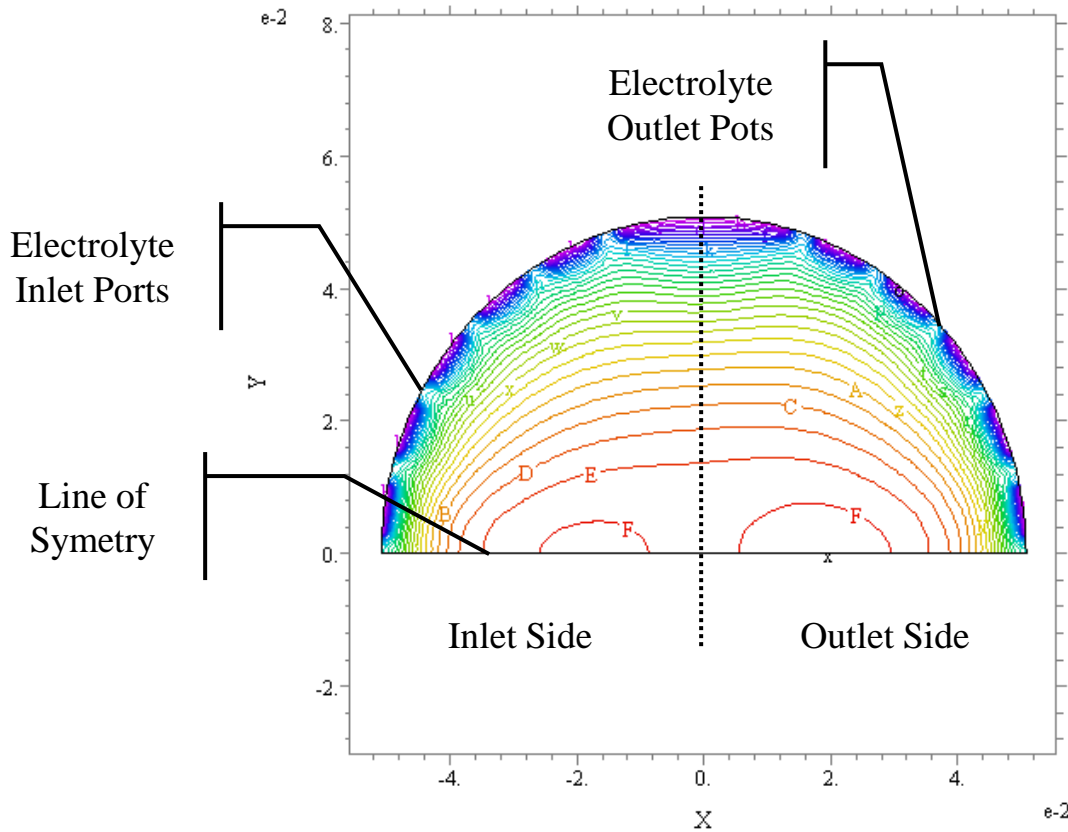
These relations can be used to specify the natural boundary condition for the pressure equation. The normal component of the gradient of P is

$$n \cdot \text{grad}(P) = n_x * dx(P) + n_y * dy(P)$$

where n_x and n_y are the direction cosines of the surface normal.

Viscous Flow through the Etching Cell

06:54:32 7/12/07
FlexPDE 5.0.10



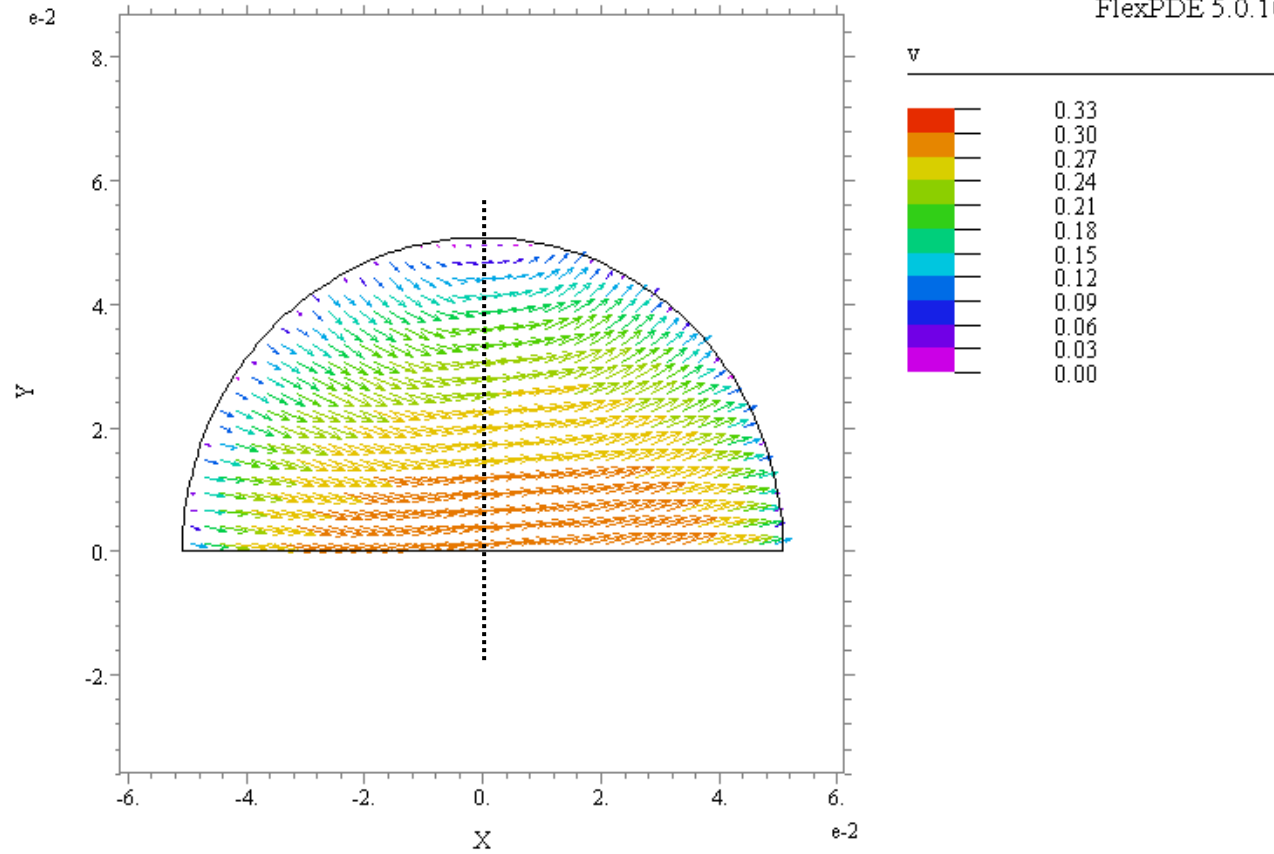
vm			
max	0.31	a:	0.00
F:	0.31	min	0.00
E:	0.30		
D:	0.29		
C:	0.28		
B:	0.27		
A:	0.26		
z:	0.25		
y:	0.24		
x:	0.23		
w:	0.22		
v:	0.21		
u:	0.20		
t:	0.19		
s:	0.18		
r:	0.17		
q:	0.16		
p:	0.15		
o:	0.14		
n:	0.13		
m:	0.12		
l:	0.11		
k:	0.10		
j:	0.09		
i:	0.08		
h:	0.07		
g:	0.06		
f:	0.05		
e:	0.04		
d:	0.03		
c:	0.02		
b:	0.01		

BIGETCH21A: Grid#2 P2 Nodes=808 Cells=377 RMS Err= 0.0119
Re= 31368.15 Integral= 9.390792e-4

Electrolytic Etching Cell Velocity Magnitude Distribution – FEA analysis using flexPDE

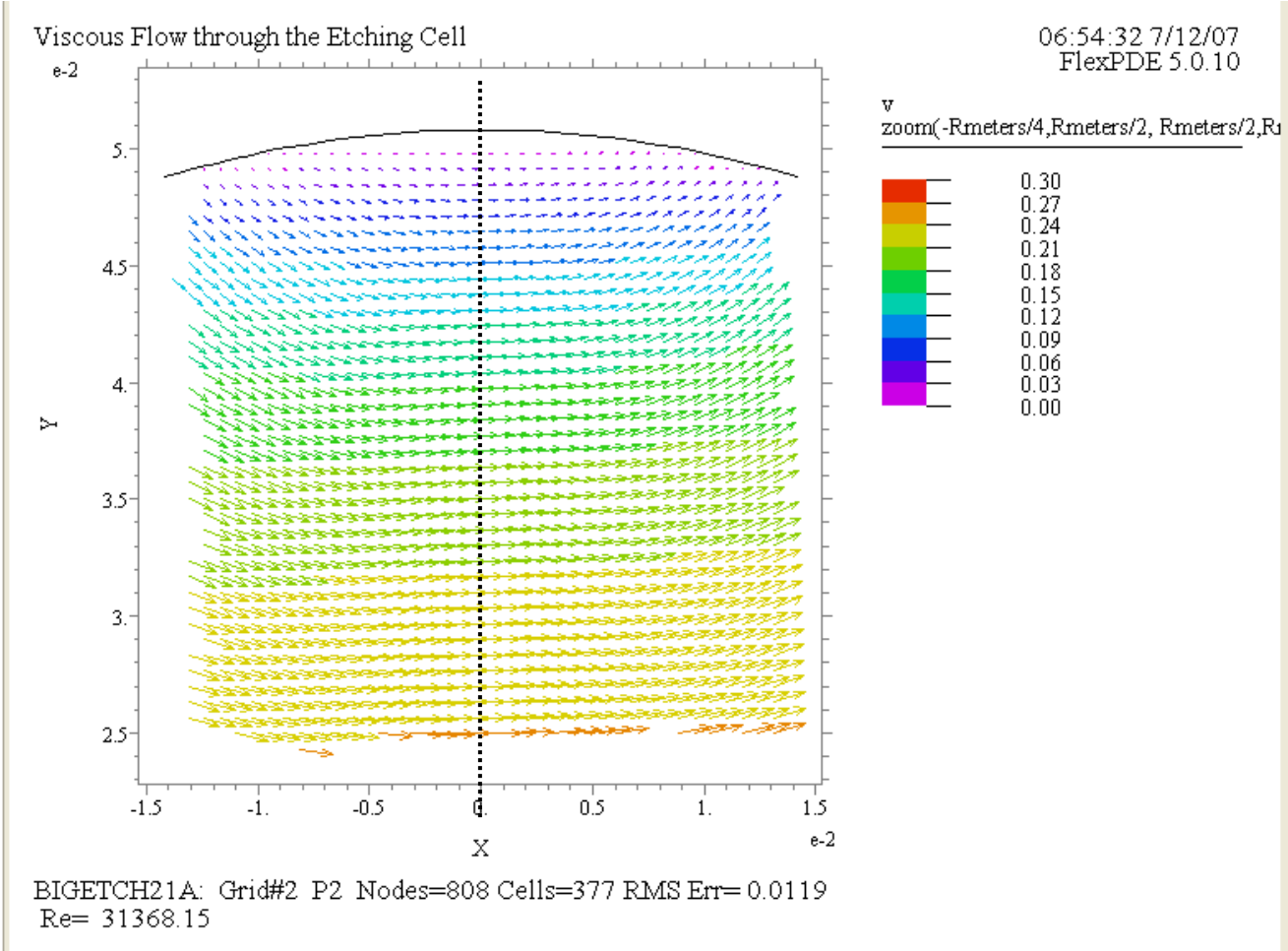
Viscous Flow through the Etching Cell

06:54:32 7/12/07
FlexPDE 5.0.10



BIGETCH21A: Grid#2 P2 Nodes=808 Cells=377 RMS Err= 0.0119
Re= 31368.15

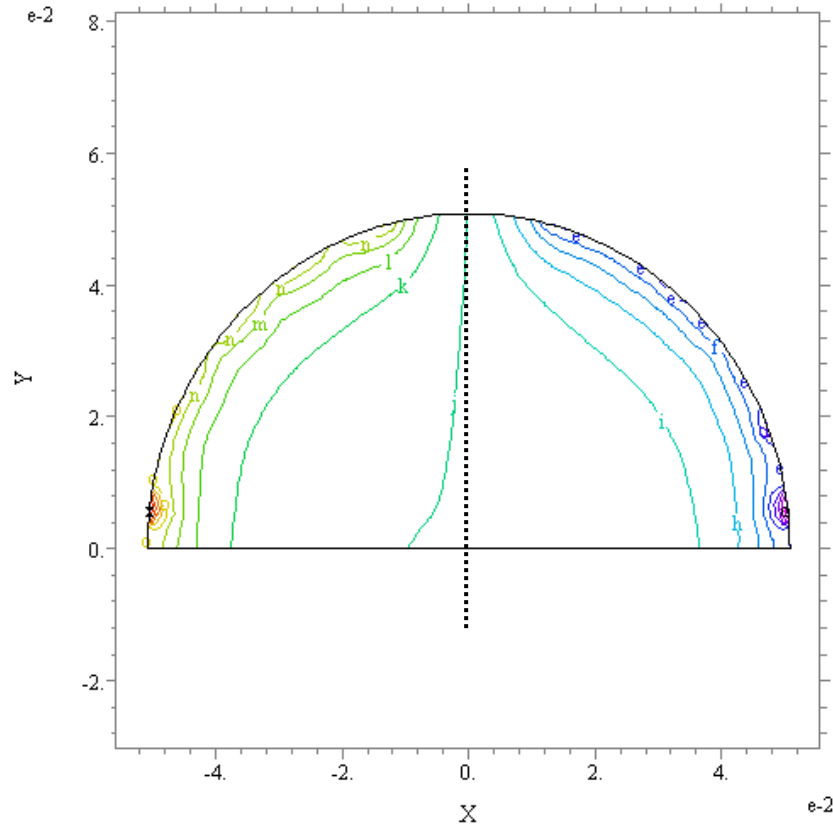
Electrolytic Etching Cell Velocity Distribution – FEA analysis using flexPDE



Electrolytic Etching Cell Velocity Distribution - Expanded – FEA analysis using flexPDE

Viscous Flow through the Etching Cell

06:54:32 7/12/07
FlexPDE 5.0.10



p

max	9.83
s	9.00
r	8.00
q	7.00
p	6.00
o	5.00
n	4.00
m	3.00
l	2.00
k	1.00
j	0.00
i	-1.00
h	-2.00
g	-3.00
f	-4.00
e	-5.00
d	-6.00
c	-7.00
b	-8.00
a	-9.00
min	-9.84

Scale = E-2

BIGETCH21A: Grid#2 P2 Nodes=808 Cells=377 RMS Err= 0.0119
Integral= -3.417964e-6

Electrolytic Etching Cell Pressure Distribution – FEA analysis using flexPDE

Summary and Conclusions

An electrolytic etching cell suitable for producing 100 mm diameter porous silicon wafers has been designed and analyzed using finite element analysis as implemented through flexPDE

The overall design and the detailed design of the individual subsystems was successful and many hundreds ... perhaps thousands of porous silicon wafers have been fabricated.